

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. **(Currently Amended)** A cleaning solution for surface treatment operations in which metal impurity contamination becomes troublesome comprising an alkaline compound, hydrogen peroxide, water and 2,2-Bis-(hydroxyethyl)-(iminotris)-(hydroxymethyl)methane [Bis Tris] ~~2,2-Bis-(hydroxyethyl)-(iminotris)-(hydroxymethyl)methan [Bis-Tris]~~ and/or 2,2-Bis-(hydroxyethyl)-(iminotris)-(hydroxymethyl)methane [Bis Tris] and nitrilotriacetic acid [NTA; CAS 139-13-9; ~~Titplex-I~~] as chelating additive(s).
2. **(Currently Amended)** A cleaning solution according to claim 1, wherein ~~characterised in that~~ the alkaline compound is chosen from the group consisting of an organic base, ammonia, ammonium hydroxide, or tetramethyl ammonium hydroxide.
3. **(Currently Amended)** A cleaning solution according to claim 1, wherein ~~characterised in that~~ the alkaline compound is chosen from the group consisting of ammonia and or ammonium hydroxide.
4. **(Currently Amended)** A cleaning solution according to claim 1, comprising 2,2-Bis-(hydroxyethyl)-(iminotris)-(hydroxymethyl)methane [Bis Tris] ~~2,2-Bis-(hydroxyethyl)-(iminotris)-(hydroxymethyl)methan [Bis-Tris]~~ in an amount in the range of 1000 to 3000 ppm.
5. **(Currently Amended)** A cleaning solution according to claim 1, comprising nitrilotriacetic acid [NTA; CAS 139-13-9; ~~Titplex-I~~] in an amount in the range of 100 to 2000 ppm.
6. **(Currently Amended)** A cleaning solution according to claim 1, comprising 2,2-Bis-(hydroxyethyl)-(iminotris)-(hydroxymethyl)methane [Bis Tris] ~~2,2-Bis-(hydroxyethyl)-(iminotris)-(hydroxymethyl)methan [Bis-Tris]~~ and nitrilotriacetic acid [NTA; CAS 139-13-9; ~~Titplex-I~~] in a total amount less than 4000 ppm.
7. **(Currently Amended)** A cleaning solution according to claim 1, comprising 2,2-Bis-(hydroxyethyl)-(iminotris)-(hydroxymethyl)methane [Bis Tris] ~~2,2-Bis-(hydroxyethyl)-(iminotris)-(hydroxymethyl)methan [Bis-Tris]~~ and nitrilotriacetic acid [NTA; CAS 139-13-9; ~~Titplex-I~~] in a total amount less than 2000 ppm.

8. **(Currently Amended)** A method for cleaning a semiconductor substrate ~~substrate(s)~~ comprising ~~the step of treatment of~~ treating the semiconductor ~~substrate~~ substrate(s) with a cleaning solution according to claim 1, and drying said semiconductor substrate ~~substrate(s)~~ after water rinsing.
9. **(Currently Amended)** A method of treatment according to claim 8, wherein ~~characterised in that~~ the treatment with cleaning solution is carried out at a temperature the range of 20 to 80 °C.
10. **(Currently Amended)** A method of treatment according to claim 8, wherein ~~characterised in that~~ the treatment with cleaning solution is carried out at normal room temperature.
11. **(Currently Amended)** A method of treatment according to claim 8, wherein ~~characterised in that~~ said cleaning solution is ~~solutions according to the invention~~ are brought into contact with a surface ~~surfaces~~ to be cleaned for a few seconds to 60 minutes.
12. **(Currently Amended)** A method of treatment according to claim 8, wherein ~~characterised in that~~ said cleaning solution is ~~solutions according to the invention~~ are brought into contact with a surface ~~surfaces~~ to be cleaned for about 15 seconds to 15 minutes.
13. **(Currently Amended)** A method for treatment of a semiconductor substrate ~~substrate(s)~~ according to claim 8, wherein the semi-conductor substrate ~~substrate(s)~~ is ~~(are)~~ immersed / dipped in the cleaning solution ~~(called dipping type cleaning)~~.
14. **(Currently Amended)** Use A method for ~~cleaning solutions according to claim 1 for for~~ surface treatment operations including cleaning, etching, polishing, film-forming, for the cleaning of substrates such as semiconductor, metal, glass, ceramics, plastic, magnetic material, superconductors comprising contacting said surface with a cleaning solution according to claim 1.